



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: V. Vaganov

Group Art Unit: 2878

Serial No.: 09/596,837

Examiner: G. Goudreau

Filed: 06/19/2000

Attorney's Docket

No.: SS-714-01

For:

METHOD FOR FABRICATING MICROSTRUCTURES WITH  
DEEP ANISOTROPIC ETCHING OF THICK SILICON WAFERS

COMMISSIONER OF PATENTS  
& TRADEMARKS  
Washington, D.C. 20231

Date of this Paper:

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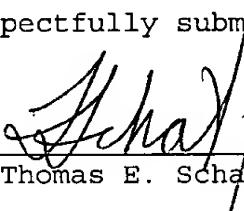
RESPONSE TO RESTRICTION REQUIREMENT

In response to the Patent Office Action mailed 11/18/2002, kindly enter the following:

Applicant respectfully traverses the merits of the request.

However, applicant elects the isotropic dry etching step claims as indicated in the Office Action (i.e. claims 26, 29-30, 33-34, 48, 51-52, 55, 85, 88, 105, 108 and 115) in the event that no generic claims are finally found allowable.

Respectfully submitted,

By   
Thomas E. Schatzel, Reg. No. 22,611

Dated: 12/12/2002

LAW OFFICES OF THOMAS E. SCHATZEL  
A Professional Corporation  
16400 Lark Avenue, Suite 240  
Los Gatos, California 95032  
Telephone: (408) 358-7733  
Facsimile: (408) 358-7720

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner of Patents and Trademarks, Washington, D.C. 20231, on 12/12/2002.

(Date of Deposit)

THOMAS E. SCHATZEL

Date of application, issuance, or registered Rep  
12/12/2002

Signature

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